



# THE DATASHEET OF RCX050N25



# 10V Drive Nch MOSFET

## RCX050N25

### ● Structure

Silicon N-channel MOSFET

### ● Features

- 1) Low on-resistance.
- 2) Low input capacitance.
- 3) High ESD.

### ● Application

Switching

### ● Packaging specifications

Type	Package	Bulk
	Code	-
	Basic ordering unit (pieces)	500
RCX050N25		○

### ● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	$V_{DSS}$	250	V	
Gate-source voltage	$V_{GSS}$	$\pm 30$	V	
Drain current	Continuous	$I_D$ *3	$\pm 5$	A
	Pulsed	$I_{DP}$ *1,3	$\pm 20$	A
Source current (Body Diode)	Continuous	$I_S$	5	A
	Pulsed	$I_{SP}$ *1	20	A
Avalanche current	$I_{AS}$ *2	2.5	A	
Avalanche energy	$E_{AS}$ *2	1.82	mJ	
Power dissipation	$P_D$ *4	30	W	
Channel temperature	$T_{ch}$	150	°C	
Range of storage temperature	$T_{stg}$	-55 to +150	°C	

\*1  $P_w \leq 10 \mu s$ , Duty cycle  $\leq 1\%$

\*2  $L = 500 \mu H$ ,  $V_{DD} = 50V$ ,  $R_G = 25 \Omega$ ,  $T_{ch} = 25^\circ C$

\*3 Limited only by maximum channel temperature allowed.

\*4  $T_C = 25^\circ C$

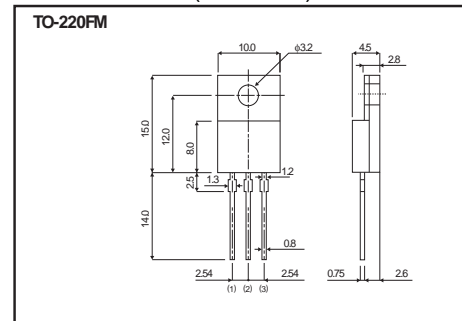
### ● Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Case	$R_{th}(ch-c)$	4.16	°C / W

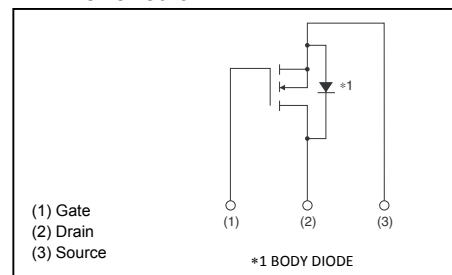
\*  $T_C = 25^\circ C$

\* Limited only by maximum channel temperature allowed.

### ● Dimensions (Unit : mm)



### ● Inner circuit



## ● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	±100	nA	$V_{GS}=\pm 30V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	250	-	-	V	$I_D=1mA, V_{GS}=0V$
Zero gate voltage drain current	$I_{DSS}$	-	-	10	μA	$V_{DS}=250V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	3.5	-	5.5	V	$V_{DS}=10V, I_D=1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	-	850	1100	mΩ	$I_D=2.5A, V_{GS}=10V$
Forward transfer admittance	$ Y_{fs} ^*$	1.2	-	-	S	$V_{DS}=10V, I_D=2.5A$
Input capacitance	$C_{iss}$	-	410	-	pF	$V_{DS}=25V$
Output capacitance	$C_{oss}$	-	30	-	pF	$V_{GS}=0V$
Reverse transfer capacitance	$C_{rss}$	-	15	-	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}^*$	-	17	-	ns	$V_{DD}\approx 125V, I_D=2.5A$
Rise time	$t_r^*$	-	18	-	ns	$V_{GS}=10V$
Turn-off delay time	$t_{d(off)}^*$	-	20	-	ns	$R_L=50\Omega$
Fall time	$t_f^*$	-	12	-	ns	$R_G=10\Omega$
Total gate charge	$Q_g^*$	-	9.0	-	nC	$V_{DD}\approx 125V, I_D=5A$
Gate-source charge	$Q_{gs}^*$	-	3.5	-	nC	$V_{GS}=10V$
Gate-drain charge	$Q_{gd}^*$	-	3.5	-	nC	$R_L=25\Omega, R_G=10\Omega$

\*Pulsed

## ● Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	$V_{SD}^*$	-	-	1.5	V	$I_s=5A, V_{GS}=0V$

\*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics ( I )

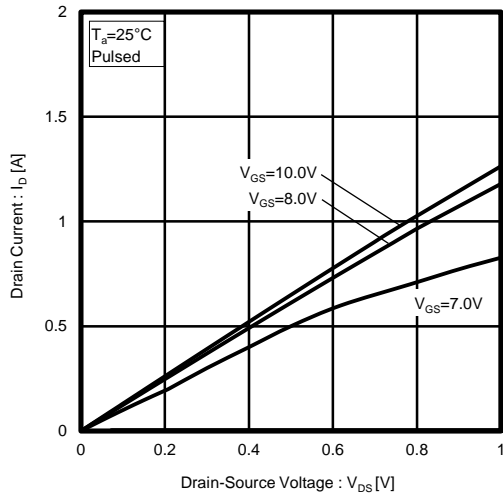


Fig.2 Typical Output Characteristics ( II )

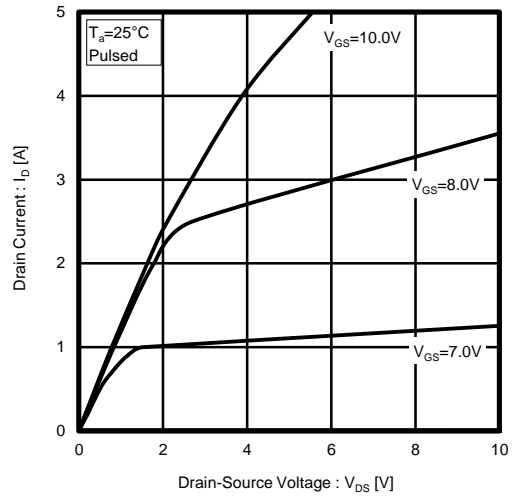


Fig.3 Typical Transfer Characteristics

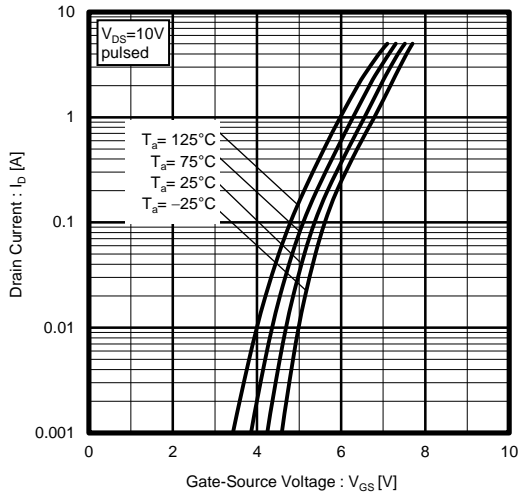


Fig.4 Gate Threshold Voltage vs. Channel Temperature

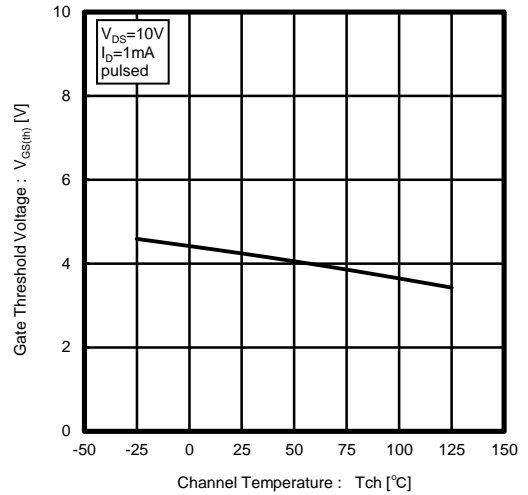


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

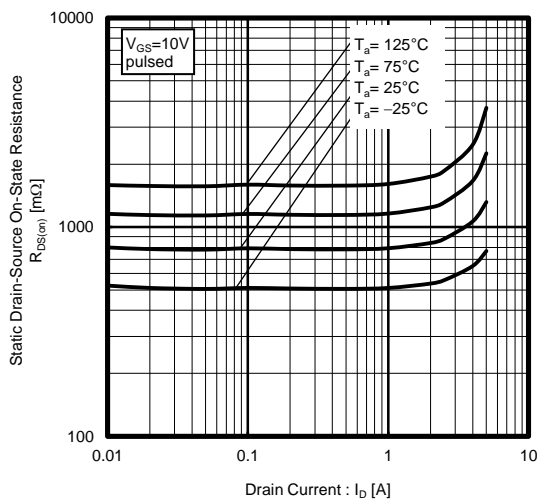


Fig.6 Static Drain-Source On-State Resistance vs. Channel Temperature

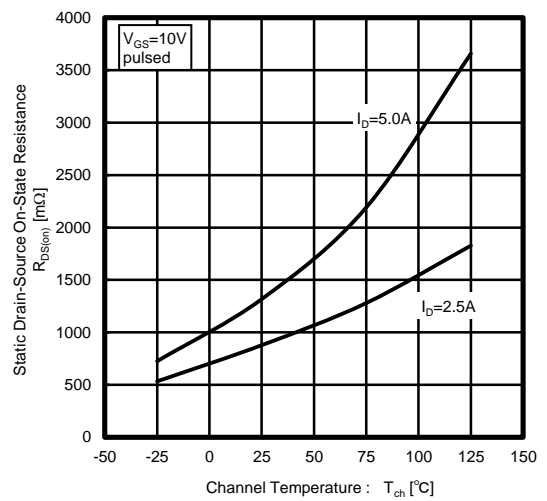


Fig.7 Forward Transfer Admittance vs. Drain Current

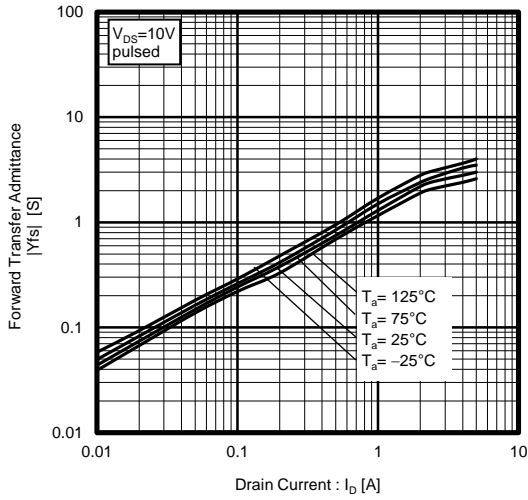


Fig.8 Source Current vs. Source-Drain Voltage

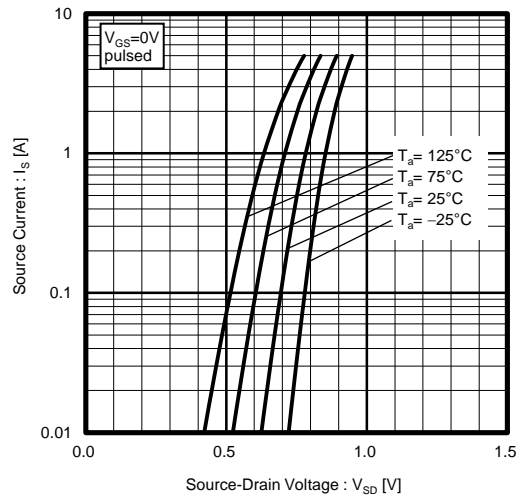


Fig.9 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

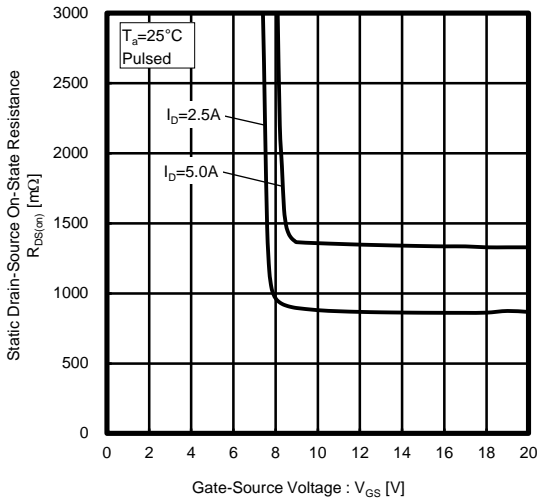


Fig.10 Switching Characteristics

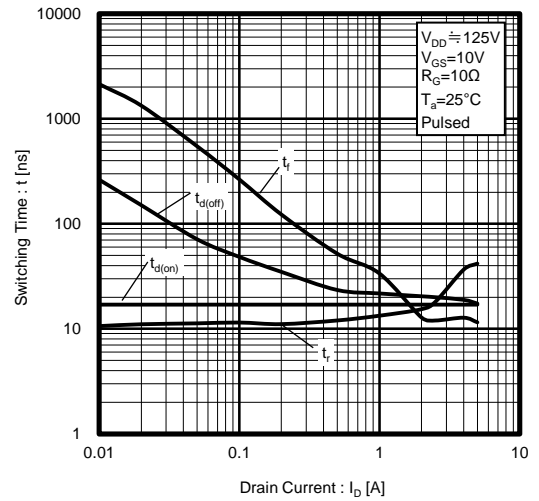


Fig.11 Dynamic Input Characteristics

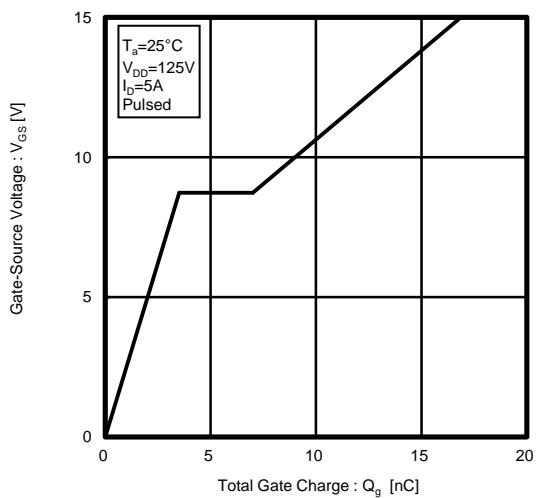


Fig.12 Typical Capacitance vs. Drain-Source Voltage

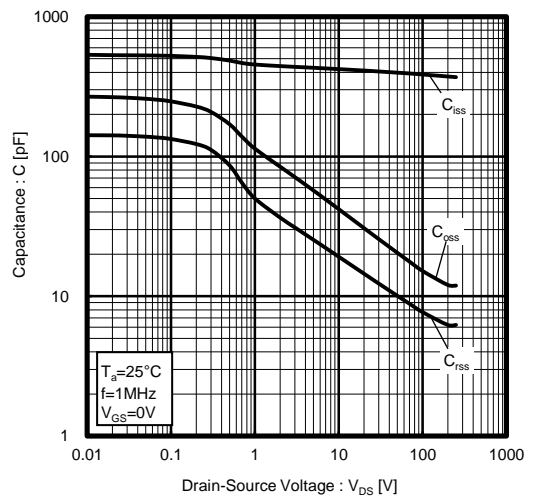


Fig.13 Reverse Recovery Time vs. Source Current

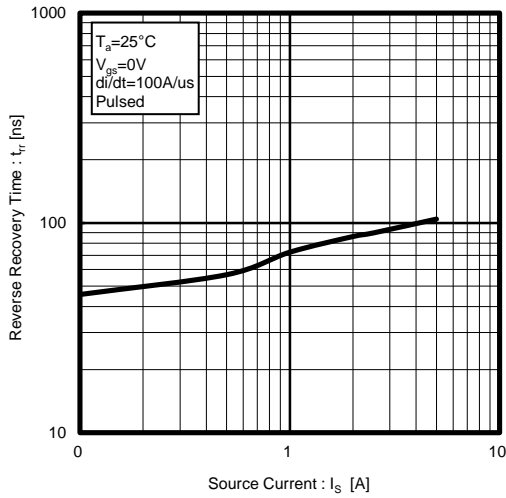


Fig.14 Maximum Safe Operating Area

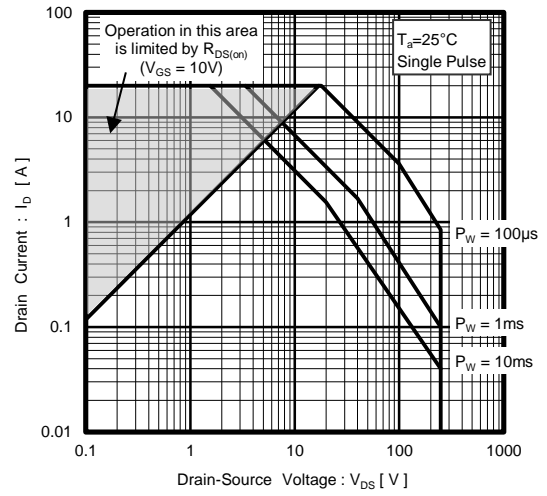
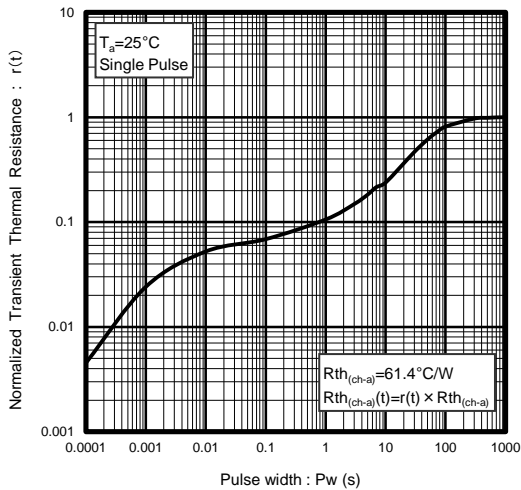


Fig.15 Normalized Transient Thermal Resistance v.s. Pulse Width



● Measurement circuits

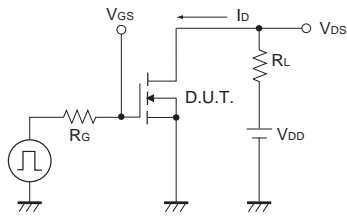


Fig.1-1 Switching Time Measurement Circuit

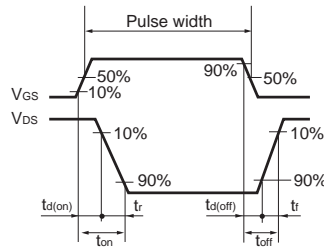


Fig.1-2 Switching Waveforms

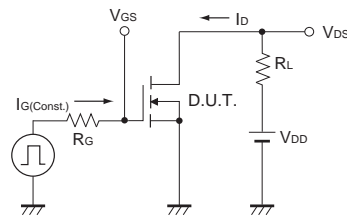


Fig.2-1 Gate Charge Measurement Circuit

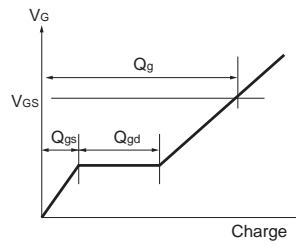


Fig.2-2 Gate Charge Waveform

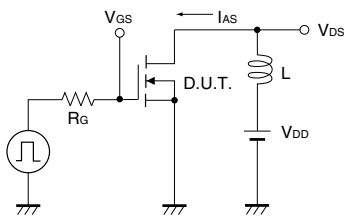


Fig.3-1 Avalanche Measurement Circuit

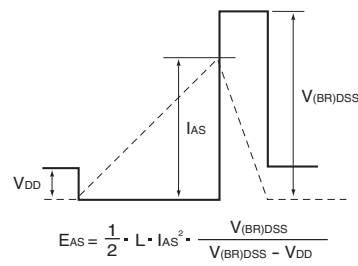


Fig.3-2 Avalanche Waveform

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